



30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _C = +25°C
-30V	$2.6m\Omega$ @ $V_{GS} = -10V$	-100A
	$3.75 m\Omega$ @ $V_{GS} = -4.5V$	-70A

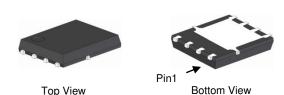
Description

This new generation MOSFET is designed to minimize $R_{DS(ON)}$ and yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

Switch

PowerDI5060-8 (Type K)

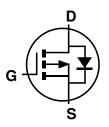


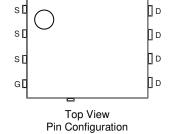
Features

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.097 grams (Approximate)





Internal Schematic

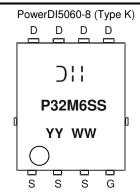
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP32M6SPS-13	PowerDI5060-8 (Type K)	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ H = Manufacturer's Marking
P32M6SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)



Characteristic				Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = -10V (Note 7) (Package Limited)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	Ι _D	-100 -70	Α
Continuous Drain Current, $V_{GS} = -10V$ (Note 6) $t \le 10s \qquad T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			Ι _D	-37 -30	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)				-400	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-2.7	Α
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	-400	Α
Avalanche Current, L = 0.1mH (Note 8)			IAS	-80	Α
Avalanche Energy, L = 0.1mH (Note 8)			E _{AS}	250	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	1.3	W	
Thermal Desistance, Junction to Ambient (Note 5)	Steady State	Б	98	00044	
Thermal Resistance, Junction to Ambient (Note 5)	t ≤ 10s	$R_{\theta JA}$	49	°C/W	
Total Power Dissipation (Note 6)		P _D	2.3	W	
The second Providence American (Alaba C)		1	54	00.00	
Thermal Resistance, Junction to Ambient (Note 6)	t ≤ 10s	$R_{\theta JA}$	27	°C/W	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	0.9	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

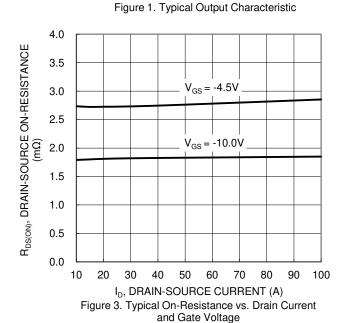
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-2.5	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	Б		1.8	2.6	mΩ	$V_{GS} = -10V, I_D = -20A$	
Static Drain-Source On-Nesistance	R _{DS(ON)}	_	2.4	3.75	11122	$V_{GS} = -4.5V, I_D = -20A$	
Diode Forward Voltage	V_{SD}	_	-0.6	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		8594		рF	V 45V V 0V	
Output Capacitance	Coss		1491		рF	$V_{DS} = -15V, V_{GS} = 0V$ -f = 1MHz	
Reverse Transfer Capacitance	C _{rss}		874		рF	1 = 1101112	
Gate Resistance	R_g	_	6.38	_	Ω	$V_{DS} = 0V$, $V_{GS} = -15mV$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	75	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	158	_	nC	V 15V L 25A	
Gate-Source Charge	Qgs	_	23.0	_	nC	$V_{DS} = -15V, I_D = -25A$	
Gate-Drain Charge	Q_{gd}	_	25.5	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	6.74	_	ns		
Turn-On Rise Time	t _R	_	5.46	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	227	_	ns	$R_{GS} = 2.7\Omega$, $I_D = -1A$	
Turn-Off Fall Time	t _F	_	108	_	ns		
Reverse Recovery Time	t _{RR}	_	37.4	_	ns	1 OF A di/dt 100 A ///-	
Reverse Recovery Charge	Q _{RR}	_	36.8	_	nC	I _F = -25A, di/dt = 100A/μs	

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).

- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.



100.0 $V_{GS} = -4.0V$ $V_{GS} = -3.5V$ 90.0 '_{GS} = -4.5V 80.0 ID, DRAIN CURRENT (A) -10.0V 70.0 60.0 $V_{GS} = -3.3V$ 50.0 40.0 $V_{GS} = -3.0V$ 30.0 20.0 $V_{GS} = -2.8V$ 10.0 $V_{GS} = -2.5V$ 0.0 0 0.5 V_{DS} , DRAIN-SOURCE VOLTAGE (V)



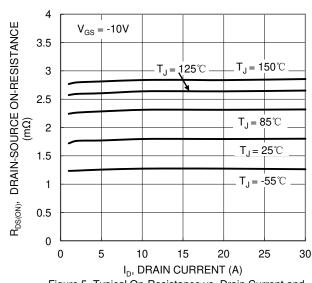
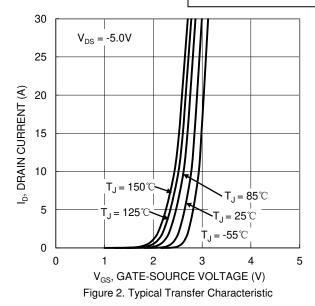
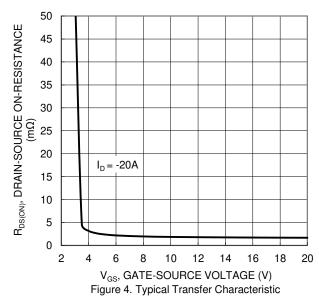


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

DMP32M6SPS





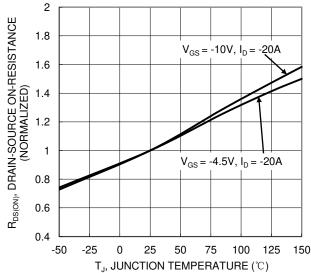


Figure 6. On-Resistance Variation with Junction Temperature





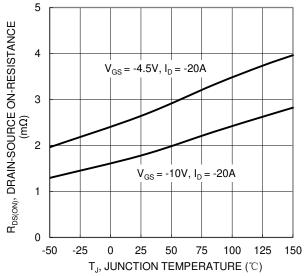
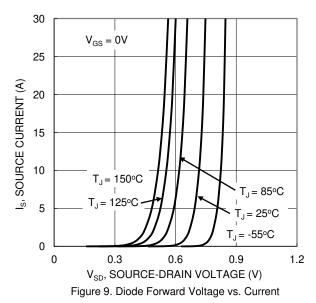


Figure 7. On-Resistance Variation with Junction Temperature



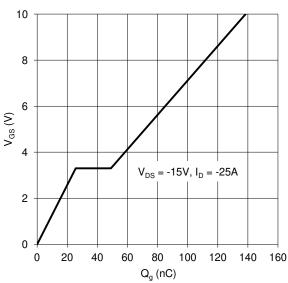


Figure 11. Gate Charge

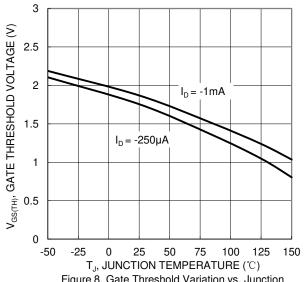
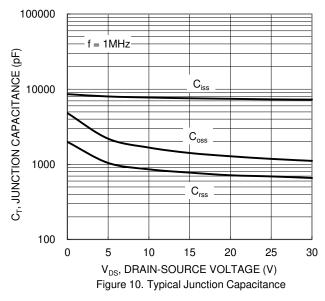


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 100 ID, DRAIN CURRENT (A) 10 $T_{J(Max)} = 150^{\circ}C$ = 100 ms $T_C = 25^{\circ}C$ Single Pulse DUT on Infinite Heatsink $V_{GS} = -10V$ 0.1 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



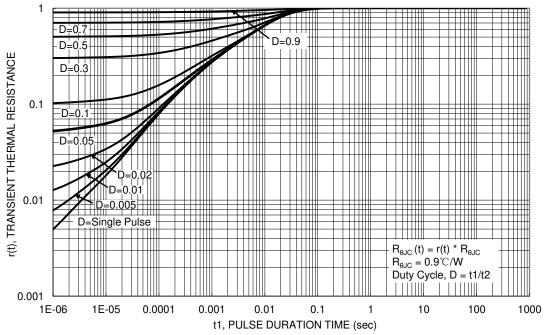


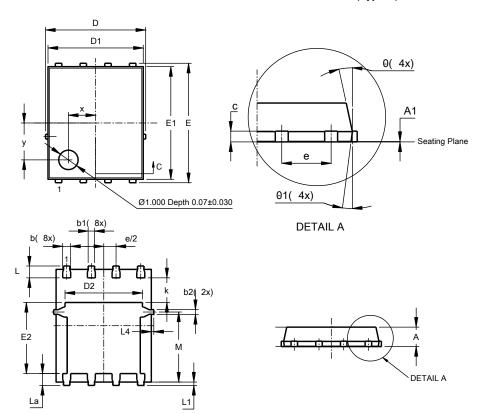
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)

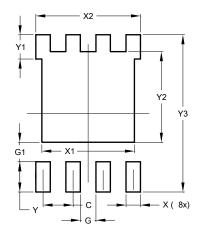


PowerDI5060-8 (Type K)						
Dim	Min	Max	Тур			
Α	0.90	1.10	1.00			
A1	0	0.05	0.02			
b	0.33	0.51	0.41			
b1	0.300	0.366	0.333			
b2	0.20	0.35	0.25			
C D	0.23	0.33	0.277			
	5.15 BSC					
D1	4.85	4.95	4.90			
D2	-	-	3.98			
Е	6.15 BSC					
E1	5.75	5.85	5.80			
E2	3.56	3.725	3.66			
е	1	.27BSC)			
k	-	-	1.27			
L	0.51	0.71	0.61			
La	0.51	0.675	0.61			
L1	0.05	0.20	0.175			
L4	-	-	0.125			
M	3.50	3.71	3.605			
X	-	-	1.400			
у	-	-	1.900			
θ	10°	12°	11°			
θ1	6°	8°	7°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8 (Type K)



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	3.910			
X2	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			

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